晧科
SHIKUES

SK02P03

30V P-Channel MOSFET

Feature

- 30V P-Channel MOSFET High Dense Design.
- Ultra low On-Resistance.
- $R_{DS(ON)}$ =100mΩ(typ.) @ V_{GS}= -10V
- $R_{DS(ON)}$ =140mΩ(typ.) @ V_{GS}= -4.5V
- Reliable and Rugged.

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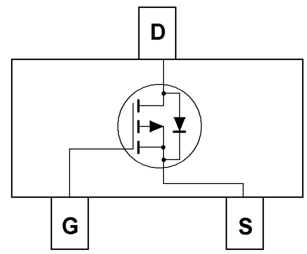

Applications

- Power Management in Portable Equipment and Battery Powered Systems and other General Application.

1. Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	±20	
I_D	Continue Drain Current	-2.6	A
I_{DM}	Pulsed Drain Current	-10	
I_S	Diode Continuous Forward Current	-2.6	A
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	150	°C/W

2. Static Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=-250μA	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-24V, V_{GS}=0V			-1	μA
		T_J=85°C			-30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	-1.0	-1.6	-2.5	V
I_{GSS}	Gate Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	V_{GS}=-10V, I_{DS}=-0.5A		100	120	mΩ
		V_{GS}=-4.5V, I_{DS}=-0.5A		140	170	
V_{SD}	Diode Forward Voltage	I_{SD}=-0.5A, V_{GS}=0V		-0.7	-1.3	V

Typical Characteristics

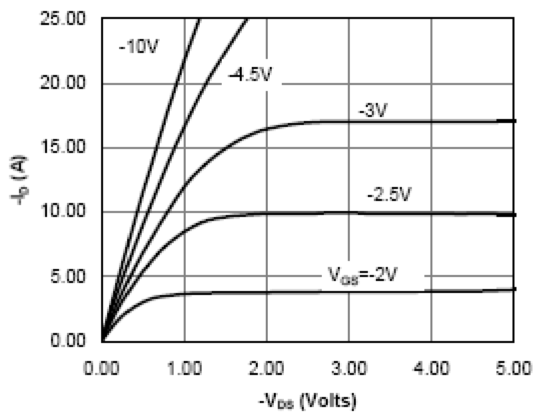

Fig 1: On-Region Characteristics

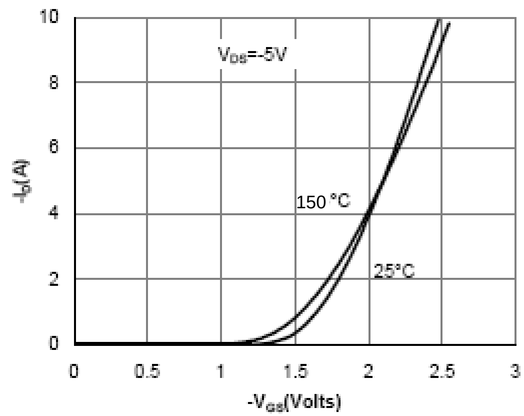

Figure 2: Transfer Characteristics

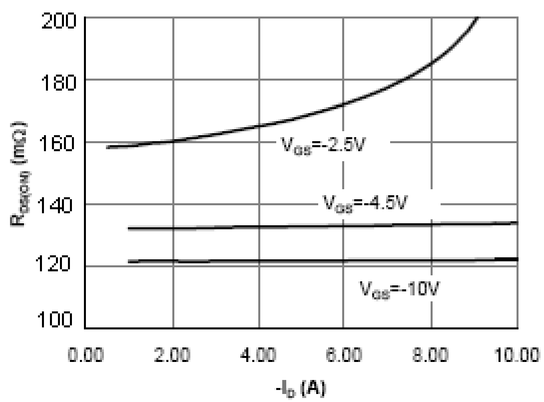

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

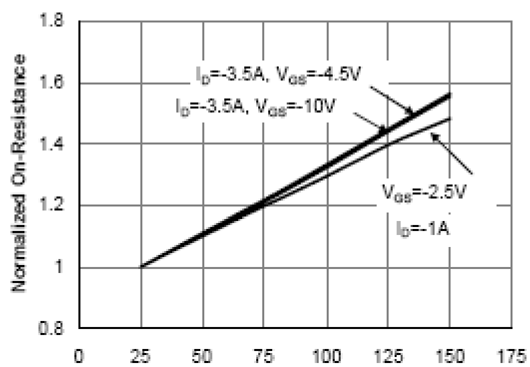

Figure 4: On-Resistance vs. Junction Temperature

Package Outline Dimensions (UNIT: mm)

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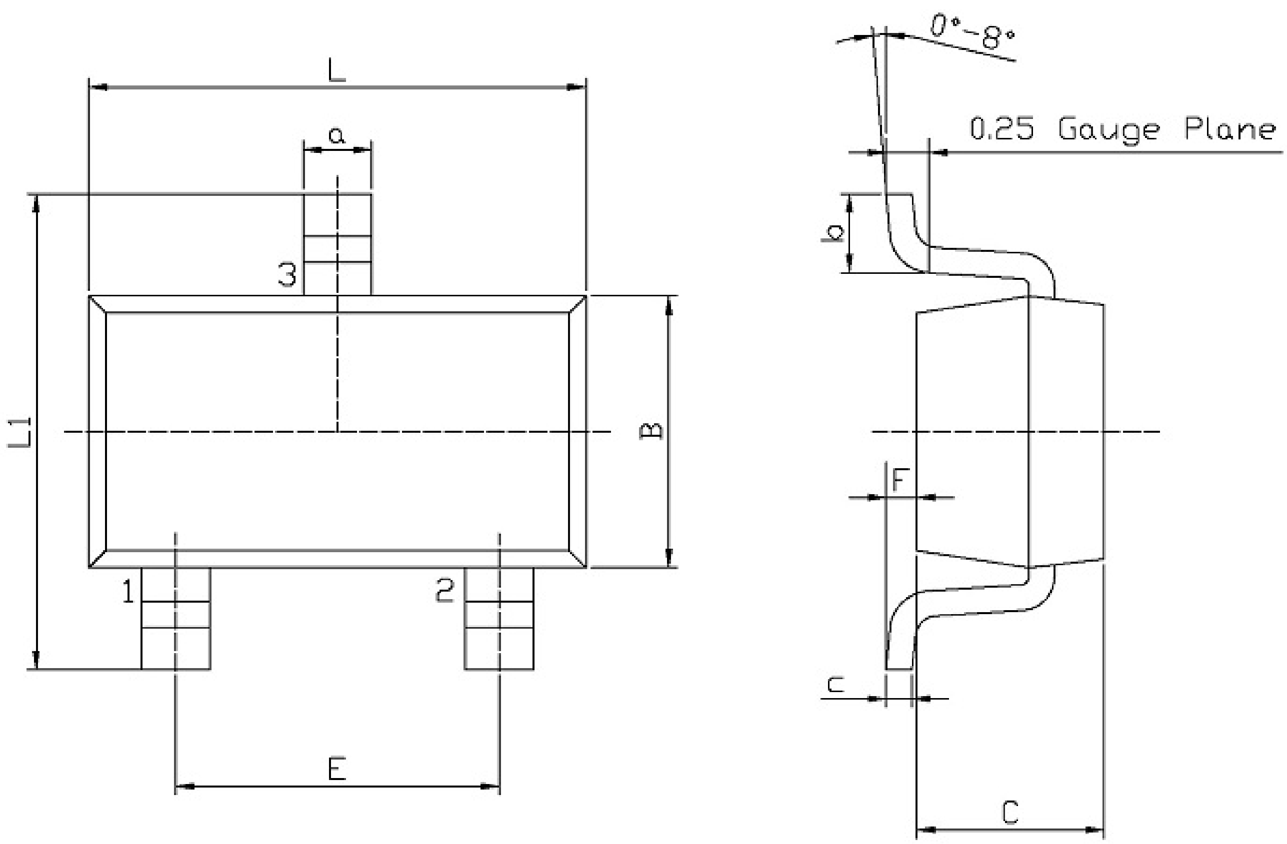

Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.82	3.02	a	0.35	0.50
B	1.50	1.70	c	0.10	0.20
C	0.90	1.30	b	0.35	0.55
L1	2.60	3.00	F	0	0.15
E	1.80	2.00			

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES(时科)]